

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,132,313 B2
APPLICATION NO. : 10/721722
DATED : November 7, 2006
INVENTOR(S) : O'Connor et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 8, line 50, in Claim 10, delete “integrally forming” and insert -- chemical vapor depositing --, therefor.

In column 10, line 4, in Claim 18, after “layer.” delete “adjacent to the number of transistors includes integrally forming a substantially planar diamond containing layer on a back side of the semiconductor chip.”.

Signed and Sealed this

Twenty-third Day of February, 2010

A handwritten signature in black ink, reading "David J. Kappos". The signature is written in a cursive, flowing style.

David J. Kappos
Director of the United States Patent and Trademark Office